

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A ceramic heater, for a semiconductor producing/examining device, comprising:

a ceramic substrate having a disc form; and

a resistance heating element formed on a surface of the ceramic substrate; thereof,

wherein

a gutter is formed along the substantially parallel to a direction of current flowing through the resistance heating element,

the ceramic substrate comprises at least one of nitride ceramics and carbide ceramics,

and

a heating face which heats a semiconductor wafer is present at a side opposite to a surface on which the resistance heating element is formed.

Claim 2 (Currently Amended): The ceramic heater for a semiconductor producing/examining device according to claim 1,

wherein ~~[[said]]~~ the gutter has a depth of 20% or more of ~~[[the]]~~ a thickness of the resistance heating element.

Claim 3 (Currently Amended): The ceramic heater for a semiconductor producing/examining device according to claim 1,

wherein a resistance value scattering in ~~[[said]]~~ the resistance heating element to ~~[[the]]~~ an average resistance value of ~~[[said]]~~ the resistance heating element is 5% or less.

Claim 4 (Currently Amended): The ceramic heater for a semiconductor producing/examining device according to claim 2,  
wherein a resistance value scattering in ~~[[said]]~~ the resistance heating element to ~~[[the]]~~ an average resistance value of ~~[[said]]~~ the resistance heating element is 5% or less.

Claim 5 (New): The ceramic heater for a semiconductor producing/examining device according to claim 1,  
wherein an oxide ceramic is formed on a surface of the ceramic substrate.

Claim 6 (New): The ceramic heater for a semiconductor producing/examining device according to claim 1,  
wherein the resistance heating element comprises plural circuits.

Claim 7 (New): The ceramic heater for a semiconductor producing/examining device according to claim 1,  
wherein the resistance heating element has a thickness of 1 to 30  $\mu\text{m}$ .

Claim 8 (New): The ceramic heater for a semiconductor producing/examining device according to claim 1,  
wherein the resistance heating element has an area resistivity of  $50\text{m}\Omega/\square$  to  $10\Omega/\square$ .

Claim 9 (New): The ceramic heater for a semiconductor producing/examining device according to claim 1,  
wherein the gutter is formed by irradiation with a laser.

Claim 10 (New): The ceramic heater for a semiconductor producing/examining device according to claim 1,

wherein the resistance heating element has a section with an aspect ratio of 10 to 5000.

Claim 11 (New): The ceramic heater for a semiconductor producing/examining device according to claim 1,

wherein the resistance heating element is formed by sintering metal particles, plating or sputtering.